

## Test #1

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Electronic Circuits (II)

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### Prob.1 (10)

We want to design the source follower shown in Fig. 1 to have voltage gain of 0.8. Using  $\frac{W}{L} = \frac{30}{0.18}$ ,  $\mu_n C_{ox} = 200 \mu A/V^2$ ,  $V_{th} = 0.4$  and  $\lambda = 0$ , determine the required gate bias voltage.

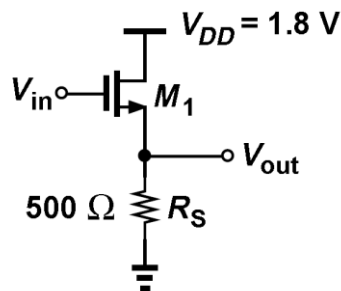
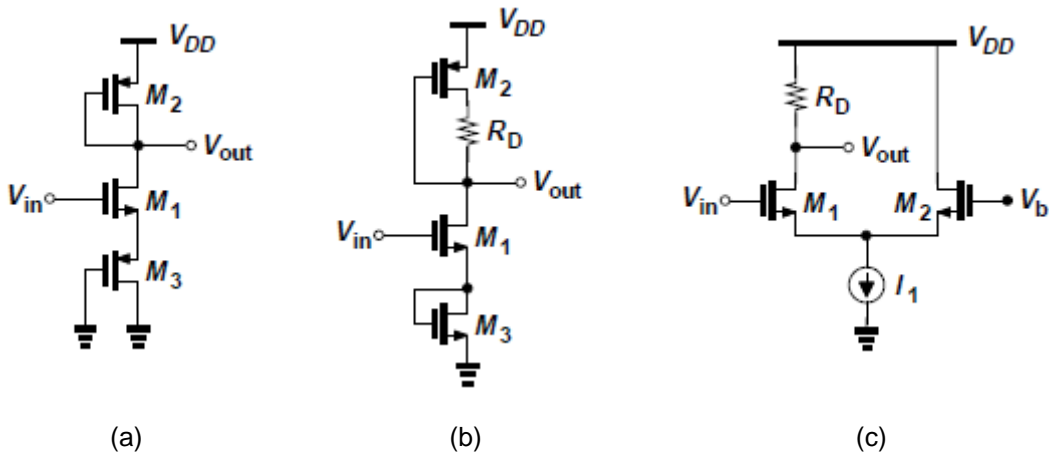


Fig. 1

### Prob. 2 (20)

Determine the voltage gain of the following CS with source degeneration amplifiers shown in Fig. 2. Assume  $\lambda=0$ . Express your answers in terms of MOS transconductances and  $R_D$ . (4 points each)



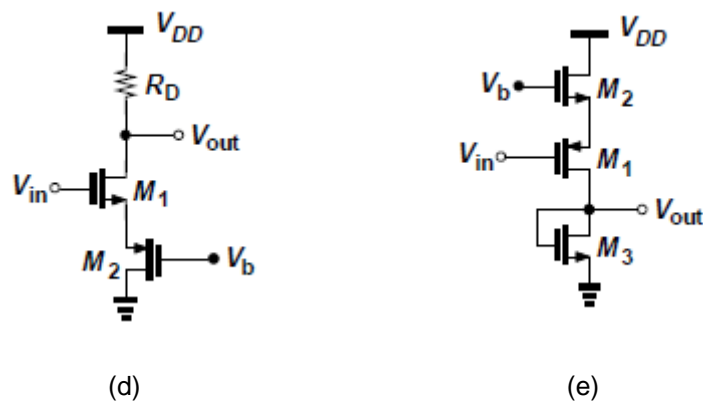
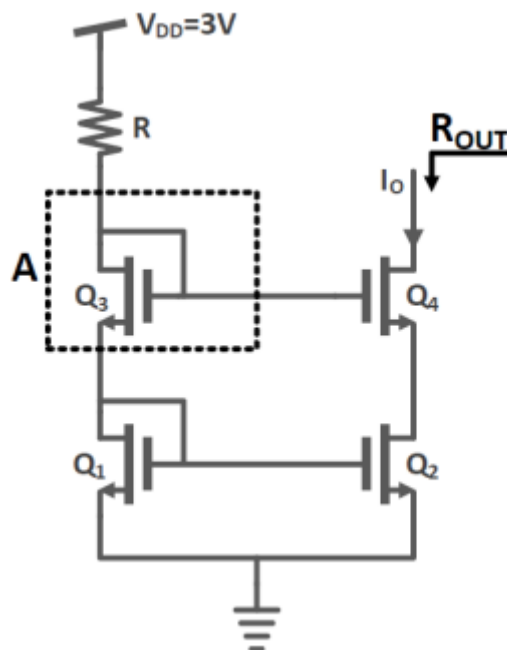


Fig. 2

**Prob. 3 (30)**

Current mirrors are often used as current sources. For better performing current sources, its output resistance should be as large as possible. In this problem, you are asked to determine the output resistance of a current-source circuit shown below. All MOS transistors are identical with  $\frac{W}{L}=100$ ,  $V_{th}=0.7V$ , and  $\mu_n C_{ox}=200\mu A/V^2$ ,  $r_o=200k\Omega$ . Use  $V_{DD}=3V$  and assume all transistors are in saturation.



**(a)(10)** Determine the numerical value for  $R$  so that  $I_o=100\mu\text{A}$ . For this part, ignore the influence of  $r_o$ .

**(b)(10)** The small-signal model for Block A is a resistor. Determine the expression for its resistance,  $R_{eq}$ . Your answer should contain only  $g_m$  and  $r_o$ .

**(c)(10)** Determine the expression for output resistance,  $R_{out}$ . Use the result obtained in (b). Your answer should contain only  $g_m$  and  $r_o$ .

**Prob. 4 (20)**

Determine the expression for  $R_p$  in the circuit of Fig. 4 such that  $I_1 = I_{REF}/2$ .

Your answer should contain only  $\frac{W}{L}, I_{REF}, \beta = \mu_n C_{ox}$ . Assume both MOS transistors are in saturation and  $\lambda=0$ .

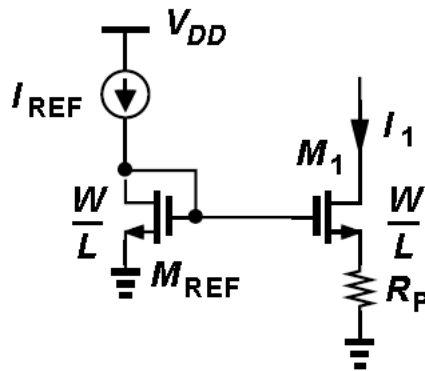
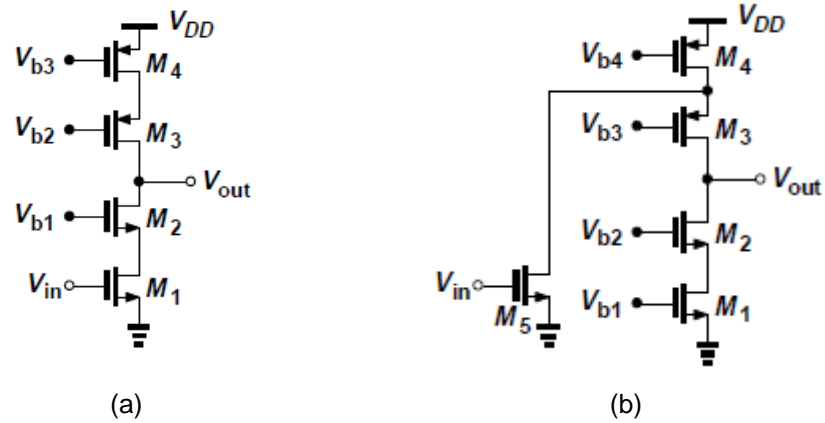


Fig. 4

**Prob. 5 (20)**



**Fig. 5**

For each of cascade circuits shown in Fig. 5, (a) determine the output impedance, (b) voltage gain. Assume each transistor  $M_n$  has output impedance  $r_{o,n}$ , which is much larger than  $1/g_{m,n}$  so that  $g_{m,n}r_{o,n} \gg 1$ .